

# Theodosia Gougousi

## List of Publications by Year in descending order

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52  
papers

1,491  
citations

346980

22  
h-index

355658

38  
g-index

52  
all docs

52  
docs citations

52  
times ranked

1952  
citing authors

#	ARTICLE	IF	CITATIONS
1	Tip-Enhanced Strong Coupling of Quantum Dot Single Photon Emitters. , 2021, , .		0
2	Low-Temperature Dopant-Assisted Crystallization of HfO <sub>2</sub> Thin Films. Crystal Growth and Design, 2021, 21, 6411-6416.	1.4	3
3	Nano-Cavity QED with Tunable Nano-Tip Interaction. Advanced Quantum Technologies, 2020, 3, 1900087.	1.8	22
4	Surface Defect Engineering of MoS <sub>2</sub> for Atomic Layer Deposition of TiO <sub>2</sub> Films. ACS Applied Materials & Interfaces, 2020, 12, 48150-48160.	4.0	7
5	Large Third-Order Nonlinearities in Atomic Layer Deposition Grown Nitrogen-Enriched TiO <sub>2</sub> Nanoscale Films. , 2020, , .		0
6	Tip-enhanced strong coupling spectroscopy, imaging, and control of a single quantum emitter. Science Advances, 2019, 5, eaav5931.	4.7	107
7	Engineering of Large Third-Order Nonlinearities in Atomic Layer Deposition Grown Nitrogen-Enriched TiO <sub>2</sub> . ACS Photonics, 2019, 6, 2966-2973.	3.2	8
8	Atomic layer deposition of Al <sub>2</sub> O <sub>3</sub> and TiO <sub>2</sub> on MoS <sub>2</sub> surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, 06A101.	0.9	7
9	In situ infrared spectroscopy study of the surface reactions during the atomic layer deposition of TiO <sub>2</sub> on GaAs (100) surfaces. Applied Surface Science, 2017, 422, 666-674.	3.1	7
10	Diffusion and interface evolution during the atomic layer deposition of TiO <sub>2</sub> on GaAs(100) and InAs(100) surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	0.9	6
11	Native oxide transport and removal during the atomic layer deposition of Ta <sub>2</sub> O <sub>5</sub> on InAs(100) surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	0.9	10
12	Atomic layer deposition of high-k dielectrics on III-V semiconductor surfaces. Progress in Crystal Growth and Characterization of Materials, 2016, 62, 1-21.	1.8	26
13	Layered Gold and Titanium Dioxide Substrates for Improved Surface Enhanced Raman Spectroscopic Sensing. Applied Spectroscopy, 2016, 70, 1375-1383.	1.2	8
14	Native Oxide Transport and Removal During Atomic Layer Deposition of TiO <sub>2</sub> Films on GaAs(100) Surfaces. ACS Applied Materials & Interfaces, 2016, 8, 1667-1675.	4.0	24
15	Characterization of the role of oxide spacers in multilayer-enhanced SERS probes. , 2015, , .		2
16	Stability and Surface Reactivity of Anatase TiO <sub>2</sub> Films. ECS Journal of Solid State Science and Technology, 2015, 4, P298-P304.	0.9	16
17	<i>In situ</i> infrared spectroscopy study of the interface self-cleaning during the atomic layer deposition of HfO <sub>2</sub> on GaAs(100) surfaces. Applied Physics Letters, 2014, 105, .	1.5	14
18	Impact of barrier thickness on transistor performance in AlN/GaN high electron mobility transistors grown on free-standing GaN substrates. Applied Physics Letters, 2014, 105, .	1.5	27

#	ARTICLE	IF	CITATIONS
19	Indium Diffusion and Native Oxide Removal during the Atomic Layer Deposition (ALD) of TiO <sub>2</sub> Films on InAs(100) Surfaces. ACS Applied Materials & Interfaces, 2013, 5, 8081-8087.	4.0	23
20	Atmospheric pressure plasma enhanced chemical vapor deposition of hydrophobic coatings using fluorine-based liquid precursors. Surface and Coatings Technology, 2013, 234, 21-32.	2.2	89
21	High Electron Velocity Submicrometer AlN/GaN MOS-HEMTs on Freestanding GaN Substrates. IEEE Electron Device Letters, 2013, 34, 199-201.	2.2	45
22	Interface Between Atomic Layer Deposition Ta <sub>2</sub> O <sub>5</sub> Films and GaAs(100) Surfaces. Journal of Physical Chemistry C, 2012, 116, 8924-8931.	1.5	15
23	AlN/GaN HEMTs with high- $\beta$ ALD HfO <sub>2</sub> or Ta <sub>2</sub> O <sub>5</sub> gate insulation. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2420-2423.	0.8	30
24	Native oxide consumption during the atomic layer deposition of TiO <sub>2</sub> films on GaAs (100) surfaces. Thin Solid Films, 2010, 518, 2006-2009.	0.8	41
25	Growth and Interface Evolution of HfO <sub>2</sub> Films on GaAs(100) Surfaces. Journal of the Electrochemical Society, 2010, 157, H551.	1.3	21
26	Atomic Layer Deposition of Metal Oxide Films on GaAs (100) surfaces. Materials Research Society Symposia Proceedings, 2009, 1155, 1.	0.1	0
27	Properties of atomic layer deposited HfO <sub>2</sub> thin films. Thin Solid Films, 2009, 517, 6576-6583.	0.8	80
28	Deposition of yttrium oxide thin films in supercritical carbon dioxide. Thin Solid Films, 2008, 516, 6197-6204.	0.8	92
29	Atomic Layer Deposition of HfO <sub>2</sub> Thin Films on Si and GaAs Substrates. Materials Research Society Symposia Proceedings, 2008, 1073, 1.	0.1	4
30	Interface of atomic layer deposited HfO <sub>2</sub> films on GaAs (100) surfaces. Applied Physics Letters, 2008, 92, .	1.5	46
31	Growth and interface of HfO <sub>2</sub> films on H-terminated Si from a TDMAH and H <sub>2</sub> O atomic layer deposition process. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 1235-1240.	0.9	29
32	Nucleation Studies of HfO <sub>2</sub> Thin Films Produced by Atomic Layer Deposition. Materials Research Society Symposia Proceedings, 2007, 996, 1.	0.1	0
33	Nucleation of HfO <sub>2</sub> atomic layer deposition films on chemical oxide and H-terminated Si. Journal of Applied Physics, 2007, 102, 034101.	1.1	52
34	Low Temperature Deposition of Metal Oxide Thin Films in Supercritical Carbon Dioxide Using Metal-organic Precursors. Materials Research Society Symposia Proceedings, 2007, 1007, 1.	0.1	1
35	Charge generation during oxidation of thin Hf metal films on silicon. Thin Solid Films, 2006, 513, 201-205.	0.8	2
36	Supercritical-carbon dioxide-assisted cyclic deposition of metal oxide and metal thin films. Applied Physics Letters, 2006, 88, 092904.	1.5	14

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37	Metal Oxide Thin Films Deposited from Metal Organic Precursors in Supercritical CO <sub>2</sub> Solutions. Chemistry of Materials, 2005, 17, 5093-5100.	3.2	63
38	Postdeposition reactivity of sputter-deposited high-dielectric-constant films with ambient H <sub>2</sub> O and carbon-containing species. Journal of Applied Physics, 2004, 95, 1391-1396.	1.1	15
39	Carbonate formation during post-deposition ambient exposure of high-k dielectrics. Applied Physics Letters, 2003, 83, 3543-3545.	1.5	55
40	Properties of La-silicate high-k dielectric films formed by oxidation of La on silicon. Journal of Applied Physics, 2003, 93, 1691-1696.	1.1	72
41	Kinetics Of Charge Generation During Formation Of Hf And Zr Silicate Dielectrics. Materials Research Society Symposia Proceedings, 2003, 765, 1.	0.1	1
42	The role of the OH species in high-k/polycrystalline silicon gate electrode interface reactions. Applied Physics Letters, 2002, 80, 4419-4421.	1.5	29
43	Run to run control in tungsten chemical vapor deposition using H <sub>2</sub> /WF <sub>6</sub> at low pressures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1931.	1.6	10
44	Process diagnostics and thickness metrology using in situ mass spectrometry for the chemical vapor deposition of W from H <sub>2</sub> /WF <sub>6</sub> . Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 1352.	1.6	17
45	Photodissociation study of CH <sub>3</sub> Br in the first continuum. Journal of Chemical Physics, 1998, 108, 5742-5746.	1.2	96
46	Measurement of the absolute yield of CO( $\hat{v}$ =3)+O products in the dissociative recombination of CO <sub>2</sub> <sup>+</sup> ions with electrons. Journal of Chemical Physics, 1998, 108, 8400-8407.	1.2	63
47	Photofragmentation of Cl <sub>2</sub> at 308 nm. Laser Chemistry, 1998, 17, 185-190.	0.5	6
48	Yield determination of OH ( $\hat{v}$ =0,1) radicals produced by the electron-ion recombination of protonated molecules. Journal of Chemical Physics, 1997, 107, 2440-2443.	1.2	8
49	Photofragmentation study of Cl <sub>2</sub> using ion imaging. Journal of Chemical Physics, 1997, 107, 43-48.	1.2	57
50	Yield determination of OH( $\hat{v}$ =0,1) radicals produced by the electron-ion recombination of H <sub>3</sub> O <sup>+</sup> ions. Journal of Chemical Physics, 1997, 107, 2430-2439.	1.2	21
51	Electron-ion recombination rate coefficient measurements in a flowing afterglow plasma. Chemical Physics Letters, 1997, 265, 399-403.	1.2	61
52	Langmuir-probe measurements in flowing-afterglow plasmas. Physical Review E, 1994, 50, 3994-4004.	0.8	39